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C23C 14/06(21)Application number : **09-223200**(71)Applicant : **TANAKA KIKINZOKU KOGYO KK**(22)Date of filing : **20.08.1997**(72)Inventor : **TAKARASAWA KATSUYUKI**
MURAKISHI YUKIHIRO**(54) PRODUCTION OF RU TARGET FOR SPUTTERING**

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain an Ru target for sputtering of a large area and high quality high in denseness and free from inside defects.**SOLUTION:** Melting and solidifying are repeated for two or more times to make an ingot, the surface or back face of this ingot is ground to make a slab, this slab as a stock is welded, its scale is increased, and, thereafter, a disk is cut out to obtain an Ru target for sputtering. In this producing method, it is preferable that, primary melting is executed by arc melting, and the secondary melting is executed by vacuum plasma melting, and the welding is executed by electron beam welding or arc welding. Furthermore, it is preferable that the melting on and after the primary and secondary ones is executed by vacuum plasma melting, and the welding is executed by electron beam welding or arc welding or vacuum plasma melting.**LEGAL STATUS**

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